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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO		
09/972,608 10/05/200		Vladimir V. Voronkov	985401/23401	4591		
321	7590 12/23/2	003	EXAN	EXAMINER		
SENNIGE	R POWERS LEAV	STEIN, S	STEIN, STEPHEN J			
ONE METR	OPOLITAN SQUAF	E				
16TH FLOOR			ART UNIT	PAPER NUMBER		
ST LOUIS, MO 63102			1775	1775		

DATE MAILED: 12/23/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

• 0	4						
		Applic	ation No.	Applicant(s)	$\overline{V}(V)$		
Office Action Summary		09/97	2,608	VORONKOV ET AL.			
		Exami	ner	Art Unit			
			en J Stein	1775			
Period fo	The MAILING DATE of this commo or Reply	ınication appears on	the cover sheet with the o	correspondence addres	S		
THE I - External feature - If the If NC I Failure - Any II	ORTENED STATUTORY PERIOD MAILING DATE OF THIS COMMUNisons of time may be available under the provisic SIX (6) MONTHS from the mailing date of this coperid for reply specified above is less than thirty period for reply is specified above, the maximum re to reply within the set or extended period for reply is specified above, the maximum do reply within the set or extended period for reply received by the Office later than three month ad patent term adjustment. See 37 CFR 1.704(b).	NICATION. ns of 37 CFR 1.136(a). In n mmunication. (30) days, a reply within the statutory period will apply a ply will, by statute, cause the s after the mailing date of thi	o event, however, may a reply be tir statutory minimum of thirty (30) day dd will expire SIX (6) MONTHS from application to become ABANDONE	mely filed ys will be considered timely. If the mailing date of this communition (35 U.S.C. § 133).	nication.		
1)⊠	Responsive to communication(s) f	iled on <u>14 October 2</u>	<u>2003</u> .				
2a)□	This action is FINAL.	2b)⊠ This action is	s non-final.				
3)□	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposit	on of Claims						
5)□ 6)⊠ 7)□	Claim(s) <u>3.4.9.11.13.15.17.19.20.</u> 4a) Of the above claim(s) is Claim(s) is/are allowed. Claim(s) <u>3.4.9-11.13.15.17.19.20.</u> Claim(s) is/are objected to. Claim(s) are subject to rest	/are withdrawn from 23,24,28-34,37-43 a	consideration. and 46 is/are rejected.	ne application.			
Applicat	ion Papers						
9)	The specification is objected to by	the Examiner.					
10)	The drawing(s) filed on is/ar						
	Applicant may not request that any ob-		•	, ,			
441	Replacement drawing sheet(s) including	-		=			
	The oath or declaration is objected	to by the Examiner	. Note the attached Office	ACTION OF TOTAL PTO-1	JZ.		
12)	under 35 U.S.C. §§ 119 and 120 Acknowledgment is made of a cla		v under 35 U.S.C. § 119(a	a)-(d) or (f).			
* \$ 13)	All b) Some * c) None of 1. Certified copies of the priori 2. Certified copies of the priori 3. Copies of the certified copie application from the Interna see the attached detailed Office ac acknowledgment is made of a claim ince a specific reference was inclue 7 CFR 1.78. 1) The translation of the foreign of acknowledgment is made of a claim afterence was included in the first see	ty documents have ty documents have is of the priority doci tional Bureau (PCT tion for a list of the on for domestic priority ded in the first sente anguage provisional of for domestic priority	peen received in Applicat uments have been receive Rule 17.2(a)). ertified copies not receive y under 35 U.S.C. § 119 (noe of the specification of application has been receive y under 35 U.S.C. §§ 120.	ed in this National Staged. e) (to a provisional appring a properties of the control of the cont	olication) a Sheet.		
Attachmen			_				
2) Notic	te of References Cited (PTO-892) te of Draftsperson's Patent Drawing Review mation Disclosure Statement(s) (PTO-1449)		5) Notice of Informal F	/ (PTO-413) Paper No(s) Patent Application (PTO-152			

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DETAILED ACTION

Election/Restrictions

1. Applicants' election of Group II in the Applicants' preliminary amendment filed October 14, 2003 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 3. Claims 3, 4, 20, 28, 29, 37-41 and 46 are rejected under 35 U.S.C. 102(b) as being anticipated by US 5,919,302 (Falster '302).

Falster '302 teaches a single crystal silicon ingot having seed cone, an end cone, and a lateral surface with the radius extending from a central axis of the ingot to the lateral surface (See Figure 5). The reference further teaches that that the ingot has a constant diameter with multiple asymmetrical regions running along the axis with one region in which vacancies are the predominant intrinsic point defect and two regions in which interstitials are the predominant intrinsic point defect (See figure 14 and col. 23, lines 13-30). Falster '302 still further teaches that the vacancy dominant region is separated by the two interstitial dominant regions which are substantially free of agglomerated defects (See Figure 14 and col. 12, lines 6-10). The reference further teaches a diameter of the ingot is 300mm (radius of the constant diameter = 150mm) (col.

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21, lines 43-65). The reference further teaches that the ingot has a length of 700mm (See Figure 14). The reference finally teaches that that the region in which vacancies are predominant intrinsic point defect has a radius which is at least 90% of the radius of the constant diameter of the ingot (See Figure 14) and that each of the regions in where silicon self interstitials have a length which is less than twice the radius of the constant diameter of the ingot (See Figure 14).

Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 5. Claims 9, 11, 13, 15, 17, 19, 22, 24, 30, 30-34, 42 and 43 are rejected under 35 U.S.C. 103(a) as being unpatentable over Falster 302'.

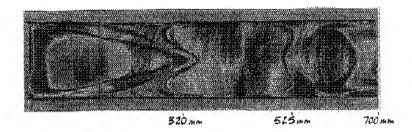
As stated above, Falster '302 teaches a single crystal silicon ingot having seed cone, an end cone, and a lateral surface with the 150mm radius extending from a central axis of the ingot to the lateral surface and multiple asymmetrical regions running along the axis with one region in which vacancies are the predominant intrinsic point defect and two regions in which interstitials are the predominant intrinsic point defect wherein the vacancy dominant region separates the two interstitial dominant regions which are substantially free of agglomerated defects.

Although Faster fails to specifically claim the claimed number of vacancy dominated regions N, the claimed length L of the ingot, and the claimed ratio L_{vac}/L_{int} , (result effective variables) absent a showing of criticality with respect to these values in would have been obvious to a person of ordinary skill in the art to maximize the length and number of vacancy dominated

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regions of the wafer in order create more usable area for creating silicon wafers. It has been held that discovering an optimum value of a result effective variable involves only routine skill in the art. In re Boesch, 617 F.2d 272, 205 USPQ 215 (CCPA 1980).

Figure 14.



Conclusion

6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Stephen Stein whose telephone number is (703) 305-0583 ((572-272-1544 after Jan 1, 2004). The examiner can normally be reached on Monday through Friday from 8:30 a.m. to 5:00 p.m. If the attempts to reach the examiner are unsuccessful, the examiner's supervisor, Deborah Jones can be reached by dialing (703) 308-3822. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group Receptionist whose phone number is (703) 308-0661. The fax phone number for this group is (703) 872-9306.

December 4, 2003

Stephen J. Stein Primary Examiner Art Unit 1775